

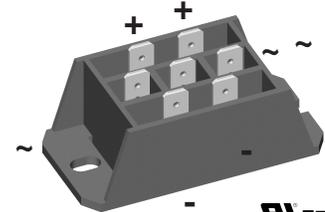
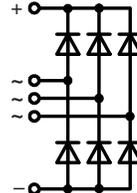
## Three Phase Rectifier Bridge

$$I_{dAV} = 72 \text{ A}$$

$$V_{RRM} = 1200-1800 \text{ V}$$

$V_{RSM}$	$V_{RRM}$	Type
V	V	
1300	1200	VUO 60-12NO3
1500	1400	VUO 60-14NO3
1700	1600	VUO 60-16NO3
1900	1800	VUO 60-18NO3*

\* delivery time on request



E72873

Symbol	Conditions	Maximum Ratings	
$I_{dAV}$ ①	$T_C = 85^\circ\text{C}$ , module	72 A	
$I_{dAVM}$ ①	module	75 A	
$I_{FSM}$	$T_{VJ} = 45^\circ\text{C}$ ; $V_R = 0$	$t = 10 \text{ ms}$ (50 Hz), sine $t = 8.3 \text{ ms}$ (60 Hz), sine	600 A 650 A
	$T_{VJ} = T_{VJM}$ $V_R = 0$	$t = 10 \text{ ms}$ (50 Hz), sine $t = 8.3 \text{ ms}$ (60 Hz), sine	540 A 600 A
$I^2t$	$T_{VJ} = 45^\circ\text{C}$ $V_R = 0$	$t = 10 \text{ ms}$ (50 Hz), sine $t = 8.3 \text{ ms}$ (60 Hz), sine	1800 A <sup>2</sup> s 1770 A <sup>2</sup> s
	$T_{VJ} = T_{VJM}$ $V_R = 0$	$t = 10 \text{ ms}$ (50 Hz), sine $t = 8.3 \text{ ms}$ (60 Hz), sine	1460 A <sup>2</sup> s 1510 A <sup>2</sup> s
$T_{VJ}$		-40...+125	$^\circ\text{C}$
$T_{VJM}$		125	$^\circ\text{C}$
$T_{stg}$		-40...+125	$^\circ\text{C}$
$V_{ISOL}$	50/60 Hz, RMS	$t = 1 \text{ min}$	3000 V~
	$I_{ISOL} \leq 1 \text{ mA}$	$t = 1 \text{ s}$	3600 V~
$M_d$	Mounting torque	(M5)	2-2.5 Nm
		(10-32 UNF)	18-22 lb.in.
Weight	typ.	50	g

### Features

- Package with DCB ceramic base plate
- Isolation voltage 3600 V~
- Planar passivated chips
- Blocking voltage up to 1800 V
- low forward voltage drop
- 1/4" fast-on terminals
- UL registered E 72873

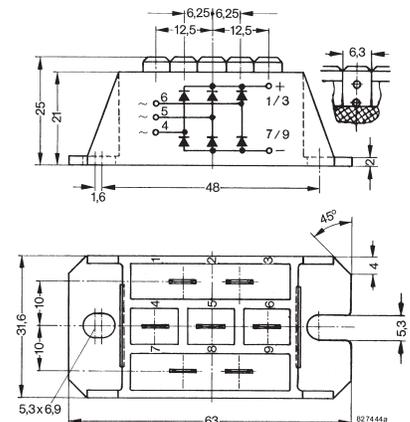
### Applications

- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- Rectifier for DC motors field current

### Advantages

- Easy to mount with two screws
- Space and weight savings
- Improved temperature and power cycling

### Dimensions in mm (1 mm = 0.0394")



**Use output terminals in parallel connection!**

Symbol	Conditions	Characteristic Values
$I_R$	$V_R = V_{RRM}$ ; $T_{VJ} = 25^\circ\text{C}$	0.3 mA
	$V_R = V_{RRM}$ ; $T_{VJ} = T_{VJM}$	5 mA
$V_F$	$I_F = 150 \text{ A}$ ; $T_{VJ} = 25^\circ\text{C}$	1.9 V
$V_{T0}$	For power-loss calculations only	0.8 V
$r_T$		6.5 m $\Omega$
$R_{thJC}$	per diode, DC current	1.2 K/W
	per module	0.2 K/W
$R_{thJH}$	per diode, DC current	1.6 K/W
	per module	0.27 K/W
$d_S$	Creep distance on surface	10 mm
$d_A$	Strike distance in air	9.4 mm
$a$	Max. allowable acceleration	50 m/s <sup>2</sup>

Data according to IEC 60747 and refer to a single diode unless otherwise stated.  
① for resistive load at bridge output.

IXYS reserves the right to change limits, test conditions and dimensions.

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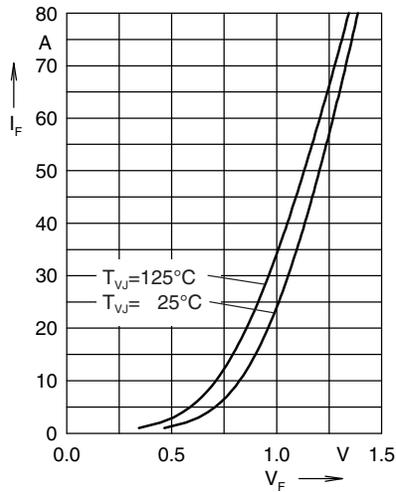


Fig. 4 Forward current versus voltage drop per diode

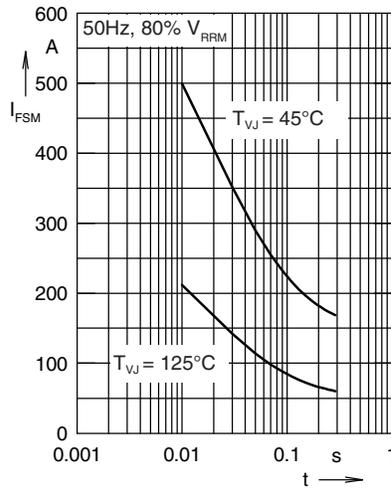


Fig. 5 Surge overload current

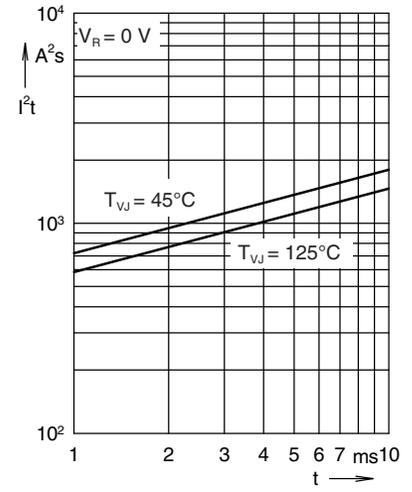


Fig. 6  $I^2t$  versus time per diode

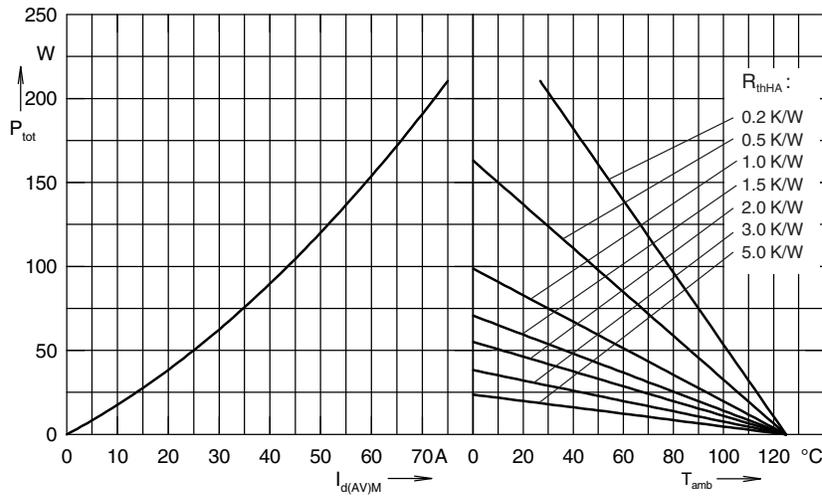


Fig. 7 Power dissipation vs. direct output current and ambient temperature

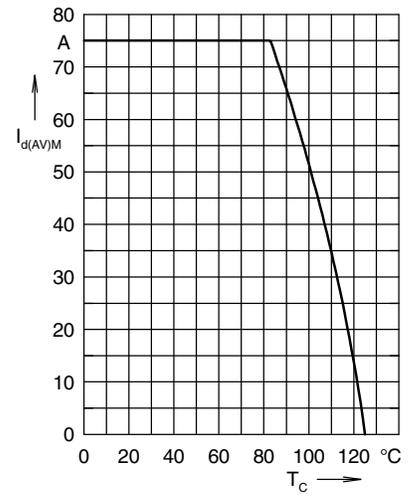


Fig. 8 Max. forward current vs. case temperature

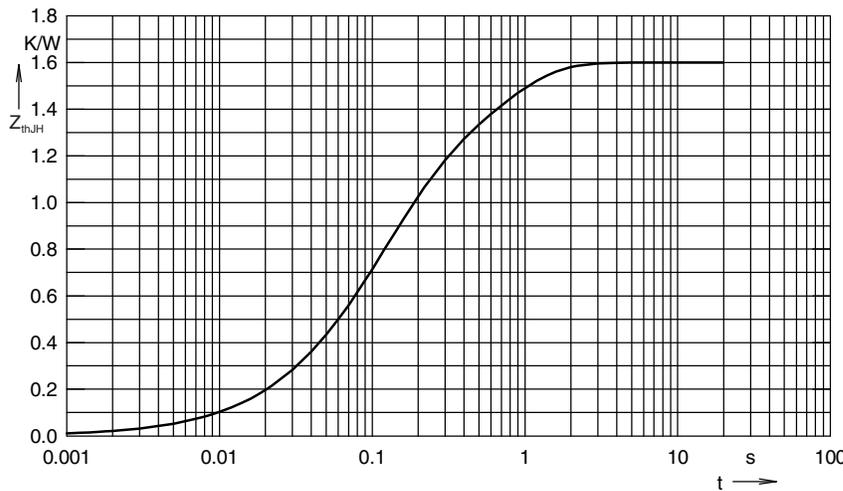


Fig. 9 Transient thermal impedance junction to heatsink

Constants for  $Z_{th,JH}$  calculation:

i	$R_{thi}$ (K/W)	$t_i$ (s)
1	0.883	0.102
2	0.098	0.103
3	0.202	0.492
4	0.417	0.62